



High temperature
batch furnace

SiC Furnace series

Implantation Annealing

The Jipelec SiC Furnace has been developed for high temperature processing of silicon carbide wafers up to 2000°C.

The sample is processed in a purified graphite enclosure. This susceptor ensures a pure environment to avoid any contamination of the samples.

The susceptor and the heating system have been designed to provide high temperature uniformity and long process capability.

The optical pyrometer and control system provides accurate and repeatable thermal control.



The SiC Furnace comes with a complete process management interface for full process control and easy data monitoring.

The SiC Furnace systems can process substrates up to 200mm.

Main features

Wafer sizes up to 200 mm
Batch capacity
Pyrometer temperature control
PID temperature control
Atmospheric and vacuum process capability
Up to 6 gas lines with MFCs
Process management software

Options

Vacuum pump
Turbomolecular pumping unit (up to 10⁻⁷ mbar)

Applications

Implantation annealing

Features

Temperature range:	700°C to 2000°C
Ramp rate:	up to 15°C/s
Pyrometer control:	500°C to 2000°C
Dimensions (L/W/H):	2000x1000x2000 mm